



# STPS30L60CW/CT/CG/CR

## POWER SCHOTTKY RECTIFIER

### MAIN PRODUCT CHARACTERISTICS

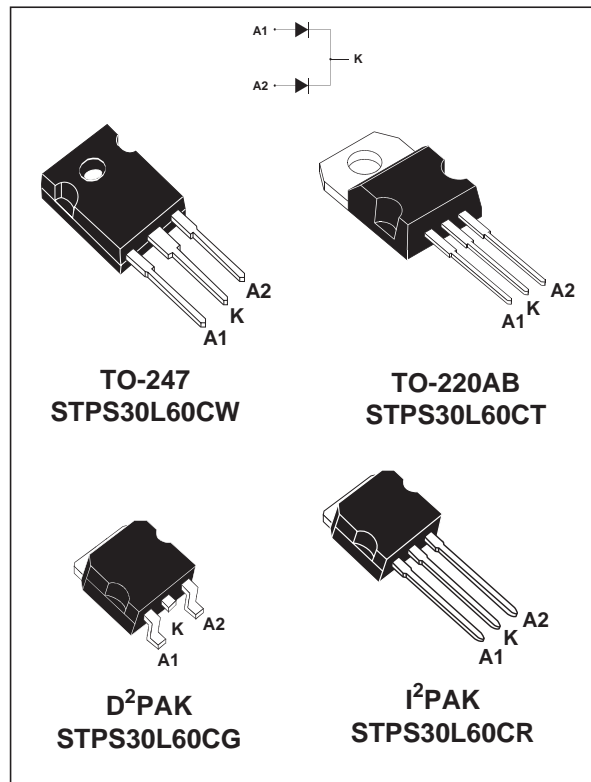
$I_{F(AV)}$	2 x 15 A
$V_{RRM}$	60 V
$T_j(\text{max})$	150°C
$V_F(\text{max})$	0.56 V

### FEATURES AND BENEFITS

- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD VOLTAGE DROP
- LOW THERMAL RESISTANCE
- AVALANCHE CAPABILITY SPECIFIED

### DESCRIPTION

Dual center tap Schottky rectifiers suited for Switched Mode Power Supplies and high frequency DC to DC converters. Packaged in TO-220, D<sup>2</sup>PAK, I<sup>2</sup>PAK and TO-247 this device is intended for use in high frequency inverters.



### ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter	Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage	60	V
$I_{F(RMS)}$	RMS forward current	30	A
$I_{F(AV)}$	Average forward current	$T_c = 130^\circ\text{C}$ $\delta = 0.5$ Per diode Per device	15 30 A
$I_{FSM}$	Surge non repetitive forward current	$t_p = 10 \text{ ms}$ Sinusoidal	230 A
$I_{RRM}$	Repetitive peak reverse current	$t_p = 2 \mu\text{s}$ square $F = 1 \text{ kHz}$	2 A
$P_{ARM}$	Repetitive peak avalanche power	$t_p = 1 \mu\text{s}$ $T_j = 25^\circ\text{C}$	7800 W
$T_{stg}$	Storage temperature range	- 65 to + 175	°C
$T_j$	Maximum operating junction temperature *	150	°C
$dV/dt$	Critical rate of rise of reverse voltage	10000	V/ $\mu\text{s}$

\*  $\therefore \frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$  thermal runaway condition for a diode on its own heatsink

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### THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	1.5	°C/W
		Total	0.8	
$R_{th(c)}$		Coupling	0.1	°C/W

When the diodes 1 and 2 are used simultaneously :  
 $\Delta T_{j(\text{diode } 1)} = P(\text{diode } 1) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode } 2) \times R_{th(c)}$

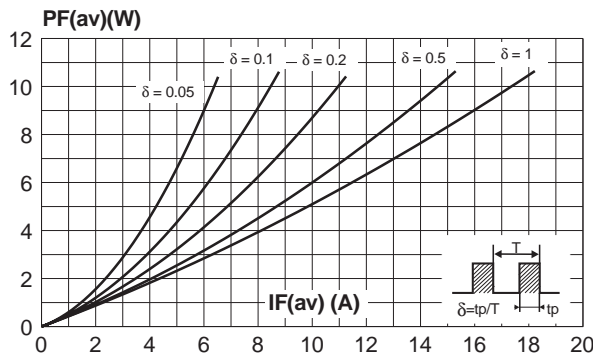
### STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
$I_R^*$	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			480	$\mu\text{A}$
		$T_j = 125^\circ\text{C}$			77	130	mA
$V_F^*$	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 15\text{ A}$			0.6	V
		$T_j = 125^\circ\text{C}$	$I_F = 15\text{ A}$		0.5	0.56	
		$T_j = 25^\circ\text{C}$	$I_F = 30\text{ A}$			0.75	
		$T_j = 125^\circ\text{C}$	$I_F = 30\text{ A}$		0.65	0.7	

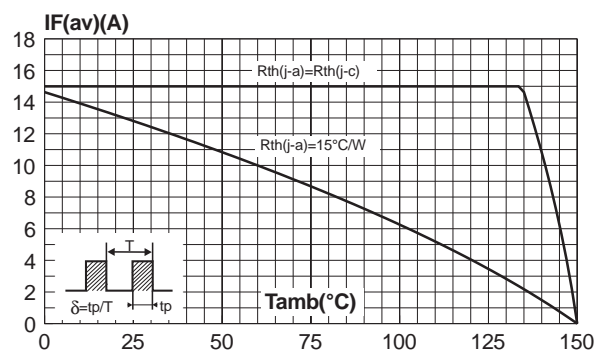
Pulse test : \*  $t_p = 380\ \mu\text{s}$ ,  $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation :  
 $P = 0.42 \times I_{F(AV)} + 0.009 I_{F(RMS)}^2$

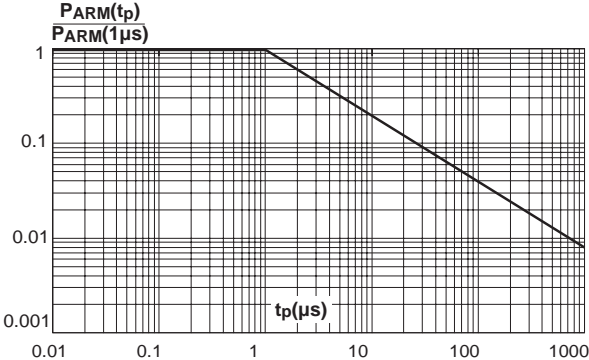
**Fig. 1:** Average forward power dissipation versus average forward current (per diode).



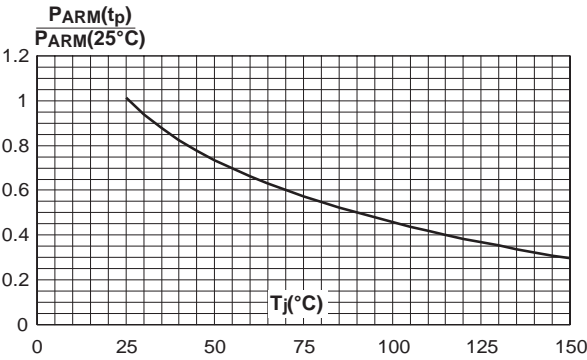
**Fig. 2:** Average forward current versus ambient temperature (delta = 0.5, per diode).



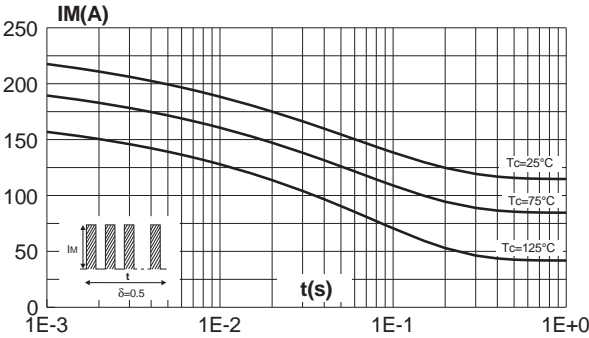
**Fig. 3:** Normalized avalanche power derating versus pulse duration.



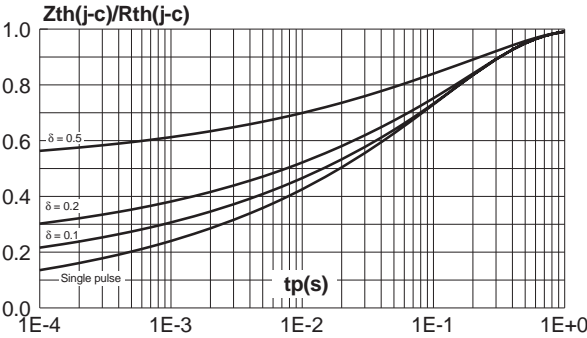
**Fig. 4:** Normalized avalanche power derating versus junction temperature.



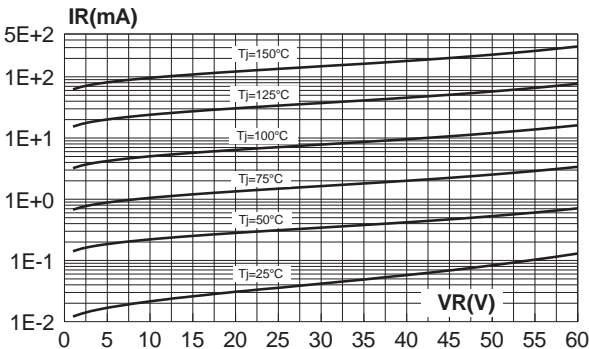
**Fig. 5:** Non repetitive surge peak forward current versus overload duration (maximum values, per diode).



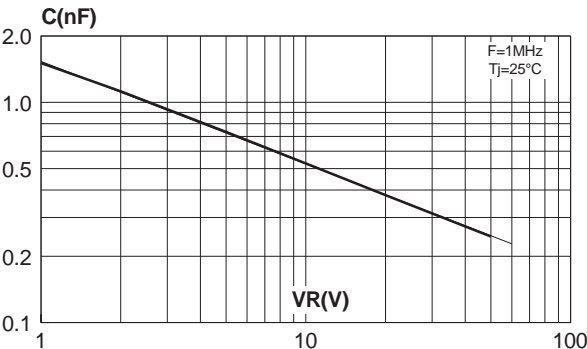
**Fig. 6:** Relative variation of thermal impedance junction to case versus pulse duration.



**Fig. 7:** Reverse leakage current versus reverse voltage applied (typical values, per diode).

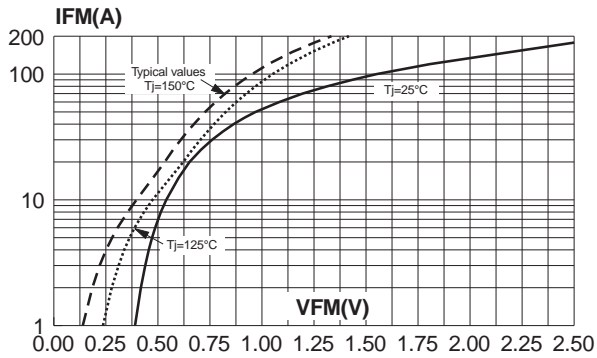


**Fig. 8:** Junction capacitance versus reverse voltage applied (typical values, per diode).

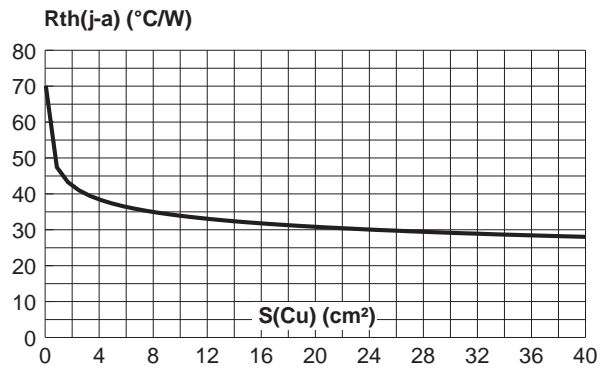


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**Fig. 9:** Forward voltage drop versus forward current (maximum values, per diode).



**Fig. 10:** Thermal resistance junction to ambient versus copper surface under tab for D<sup>2</sup>PAK (Epoxy printed circuit board FR4, copper thickness: 35µm)



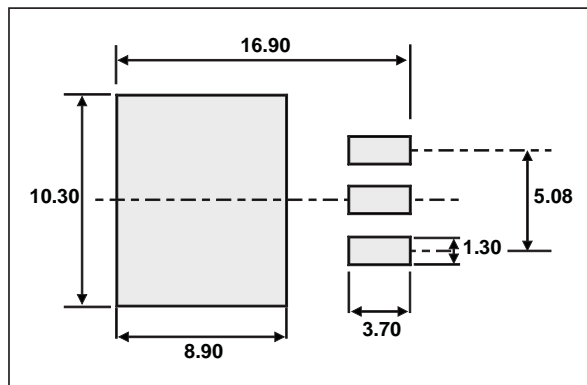
## PACKAGE MECHANICAL DATA

### D<sup>2</sup>PAK

\* FLAT ZONE NO LESS THAN 2mm

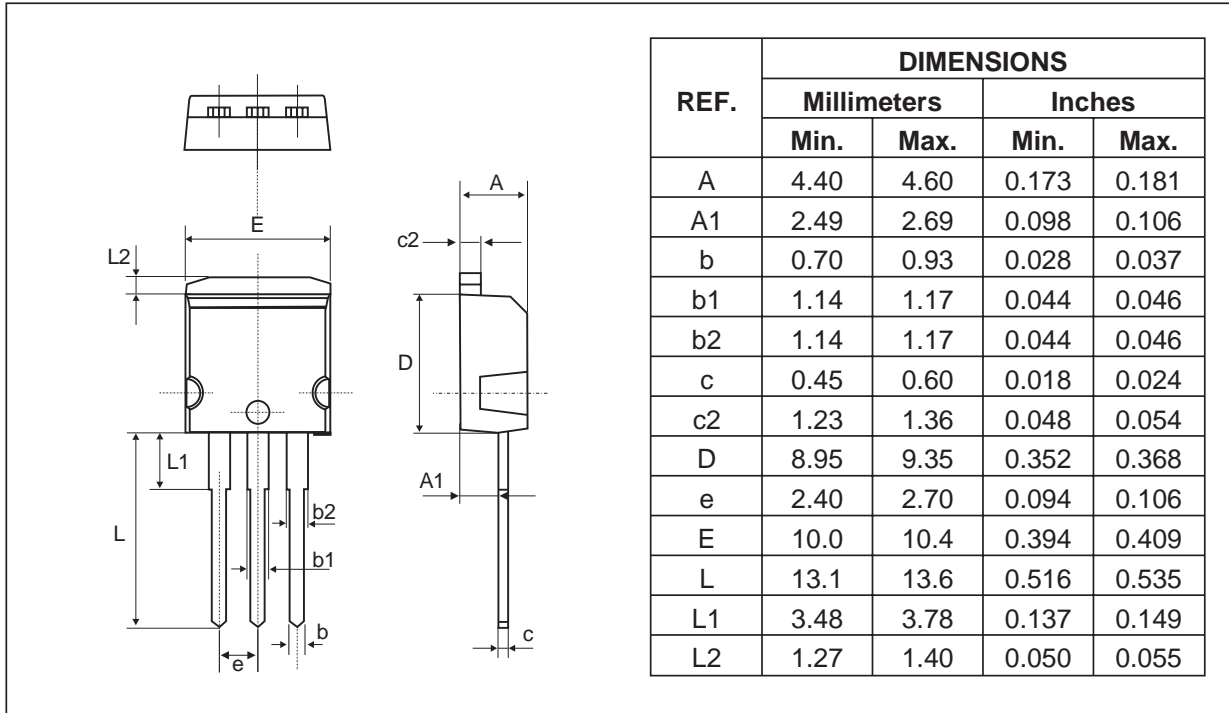
REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.49	2.69	0.098	0.106
A2	0.03	0.23	0.001	0.009
B	0.70	0.93	0.027	0.037
B2	1.14	1.70	0.045	0.067
C	0.45	0.60	0.017	0.024
C2	1.23	1.36	0.048	0.054
D	8.95	9.35	0.352	0.368
E	10.00	10.40	0.393	0.409
G	4.88	5.28	0.192	0.208
L	15.00	15.85	0.590	0.624
L2	1.27	1.40	0.050	0.055
L3	1.40	1.75	0.055	0.069
M	2.40	3.20	0.094	0.126
R	0.40 typ.		0.016 typ.	
V2	0°	8°	0°	8°

## FOOTPRINT



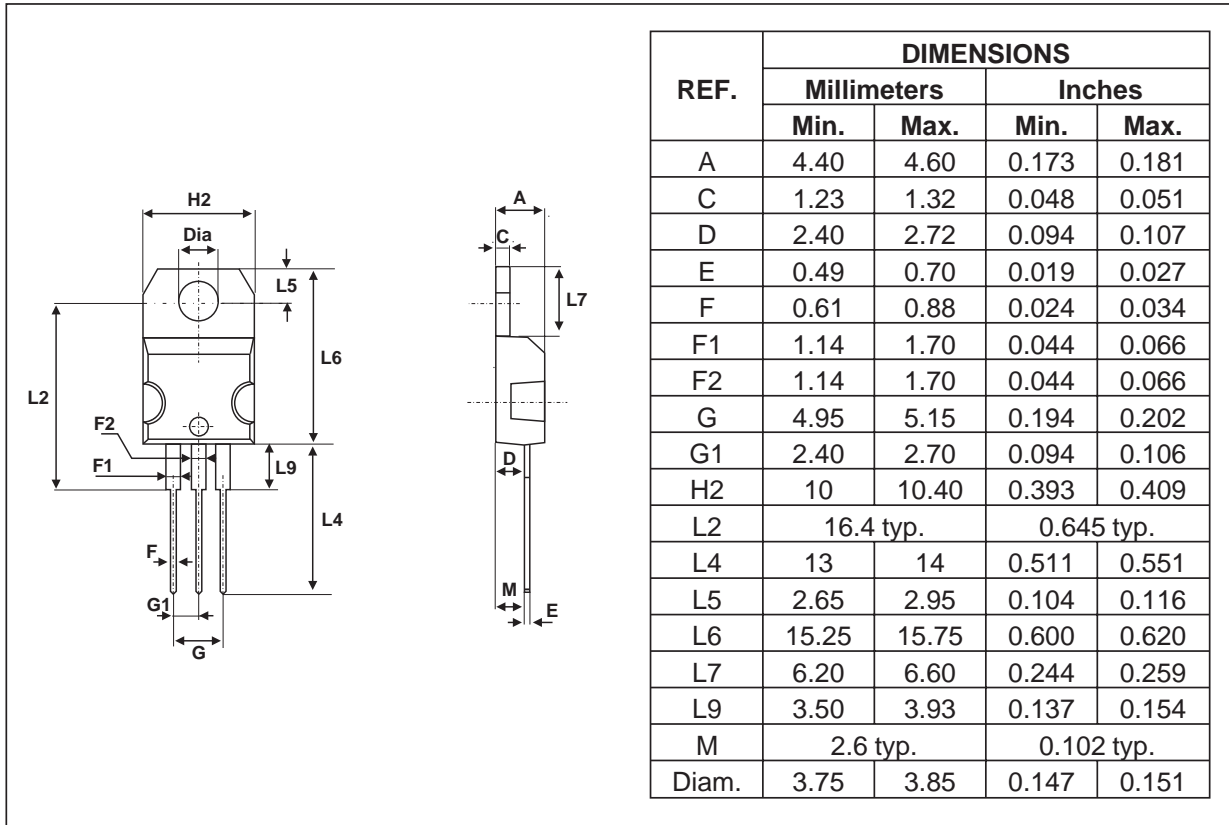
PACKAGE MECHANICAL DATA

I<sup>2</sup>PAK



PACKAGE MECHANICAL DATA

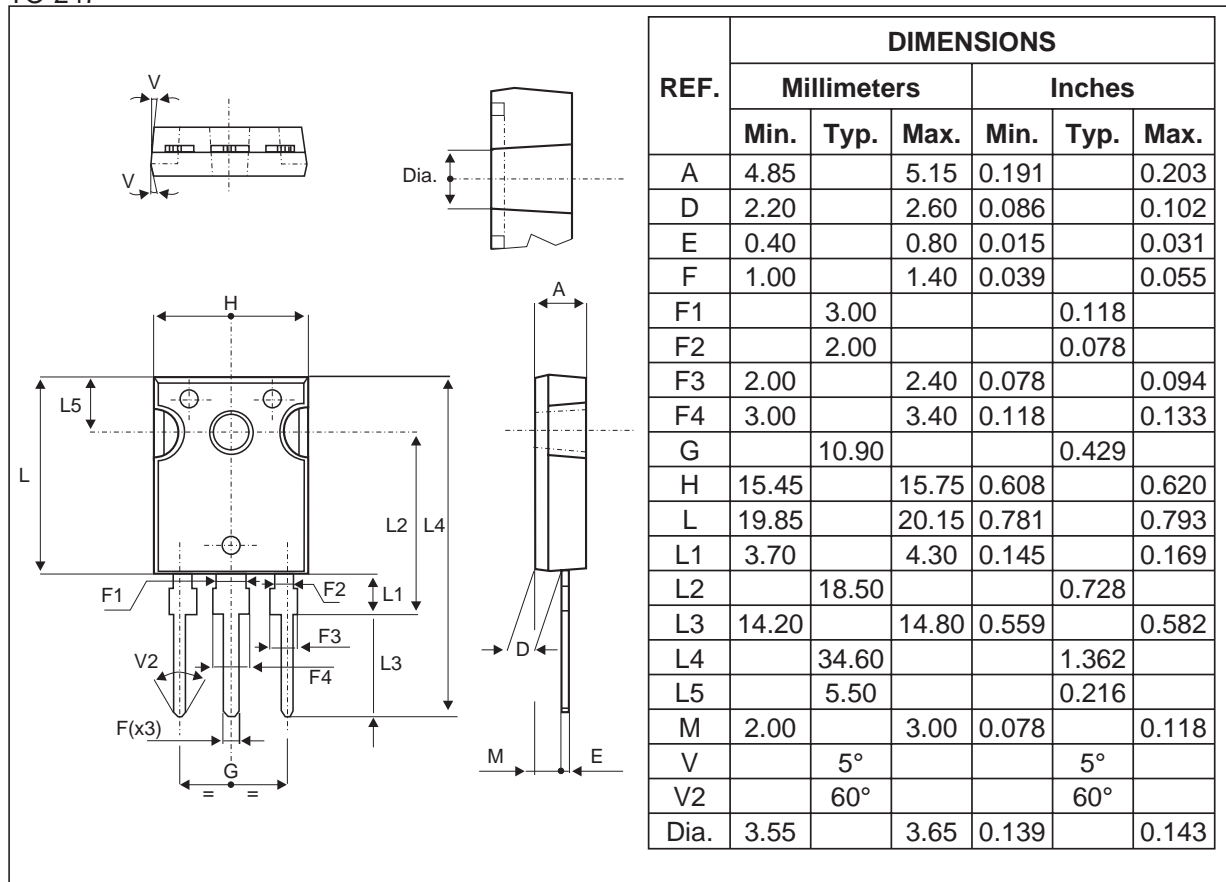
TO-220AB



**STPS30L60CW/CT/CG/CR**

**PACKAGE MECHANICAL DATA**

TO-247



- COOLING METHOD : C
- RECOMMENDED TORQUE VALUE : 0.8M.N
- MAXIMUM TORQUE VALUE : 1.0M.N

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS30L60CW	STPS30L60CW	TO-247	4.4g	50	Tube
STPS30L60CT	STPS30L60CT	TO-220AB	2.3g	50	Tube
STPS30L60CG	STPS30L60CG	D <sup>2</sup> PAK	1.5g	50	Tube
STPS30L60CR	STPS30L60CR	I <sup>2</sup> PAK	1.49 g	50	Tube

- EPOXY MEETS UL94,V0

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